Maximum Ratings / Höchstzulässige Werte

Parameter	Condition		Symbol	Datasheet values max.	Unit
Transistor Inverter **Transistor Wechselrichter**					
Collector-emitter break down voltage Kollektor-Emitter-Sperrspannung			V_{CE}	600	V
DC collector current Kollektor-Dauergleichstrom	T_j=150°C	T_h=80°C, T_c=80°C	I_C	17 20, limited by wires	A
Repetitive peak collector current Periodischer Kollektorspitzenstrom	t_p=1ms	T_h=80°C	I_{cpuls}	34	A
Power dissipation per IGBT Verlustleistung pro IGBT	T_j=150°C	T_h=80°C T_c=80°C	P_{tot}	43 66	W
Gate-emitter peak voltage Gate-Emitter-Spitzenspannung			V_{GE}	±20	V
SC withstand time Kurzschlußverhalten	Tj≤150°C V_{CE}=V_{CEBR}	V_{GE}=15V	t_{SC}	10	us
Diode Inverter **Diode Wechselrichter**					
DC forward current Dauergleichstrom	T_j=150°C	T_h=80°C, T_c=80°C	I_F	20 20, limited by wires	A
Repetitive peak forward current Periodischer Spitzenstrom	t_p=1ms	T_h=80°C	I_{FRM}	39	A
Power dissipation per Diode Verlustleistung pro Diode	T_j=150°C	T_h=80°C T_c=80°C	P_{tot}	29 44	W
Thermal properties **Thermische Eigenschaften**					
max. Chip temperature max. Chiptemperatur			T_{jmax}	150	°C
Storage temperature Lagertemperatur			T_{stg}	-40…+125	°C
Operation temperature Betriebstemperatur			T_{op}	-40…+125	°C
Insulation properties **Modulisolation**					
Insulation voltage Isolationsspannung		t=1min	V_{is}	4000	Vdc
Creepage distance Kriechstrecke				min 12,7	mm
Clearance Luftstrecke				min 12,7	mm

Characteristic values

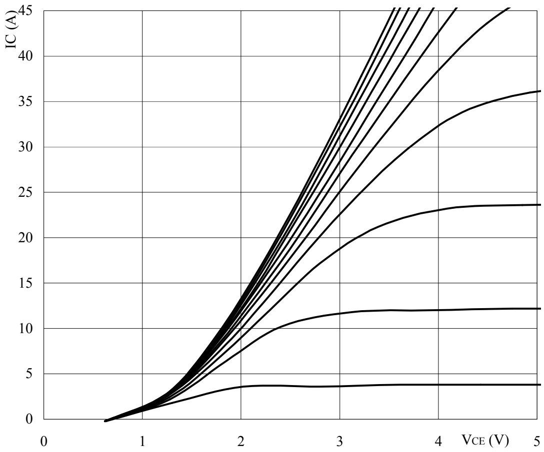
Description	Symbol	Conditions					Datasheet values			Unit
		T(C°)	Other conditions (Rgon-Rgoff)	VGE(V) VGS(V)	VR(V) VCE(V) VDS(V)	IC(A) IF(A) Id(A)	Min	Typ	Max	
Transistor Inverter, inductive load **Transistor Wechselrichter**										
Gate emitter threshold voltage	$V_{GE(th)}$	Tj=25°C	VCE=VGE			0,0004	3	4	5	V
Gate-Schwellenspannung		Tj=125°C								
Collector-emitter saturation voltage	$V_{CE(sat)}$	Tj=25°C		15		15		2,1	2,65	V
Kollektor-Emitter Sättigungsspannung		Tj=125°C						2,35		
Collector-emitter cut-off	I_{CES}	Tj=25°C		0	600				0,1	mA
Kollektor-Emitter Reststrom		Tj=125°C							2	
Gate-emitter leakage current	I_{GES}	Tj=25°C		25	0				200	nA
Gate-Emitter Reststrom		Tj=125°C								
Integrated Gate resistor	R_{gint}							-		Ohm
Integrirter Gate Widerstand										
Turn-on delay time	$t_{d(on)}$	Tj=25°C	Rgon=40Ohm	15	300	15				ns
Einschaltverzögerungszeit		Tj=125°C	Rgoff=20Ohm					19		
Rise time	t_r	Tj=25°C	Rgon=40Ohm	15	300	15				ns
Anstiegszeit		Tj=125°C	Rgoff=20Ohm					16		
Turn-off delay time	$t_{d(off)}$	Tj=25°C	Rgon=40Ohm	15	300	15				ns
Abschaltverzögerungszeit		Tj=125°C	Rgoff=20Ohm					242		
Fall time	t_f	Tj=25°C	Rgon=40Ohm	15	300	15				ns
Fallzeit		Tj=125°C	Rgoff=20Ohm					27		
Turn-on energy loss per pulse	E_{on}	Tj=25°C	Rgon=40Ohm	15	300	15				mWs
Einschaltverlustenergie pro Puls		Tj=125°C	Rgoff=20Ohm					0,300		
Turn-off energy loss per pulse	E_{off}	Tj=25°C	Rgon=40Ohm	15	300	15				mWs
Abschaltverlustenergie pro Puls		Tj=125°C	Rgoff=20Ohm					0,349		
Input capacitance	C_{ies}	Tj=25°C	f=1MHz	0	25			0,8	0,96	nF
Eingangskapazität		Tj=125°C								
Output capacitance	C_{oss}	Tj=25°C	f=1MHz	0	25			0,084	0,101	nF
Ausgangskapazität		Tj=125°C								
Reverse transfer capacitance	C_{rss}	Tj=25°C	f=1MHz	0	25			0,052	0,062	nF
Rückwirkungskapazität		Tj=125°C								
Gate charge	Q_{Gate}	Tj=25°C		15	480	15		76	99	nC
Gate Ladung		Tj=125°C								
Thermal resistance chip to heatsink per chip Wärmewiderstand Chip-Kühlkörper pro Chip	R_{thJH}		Thermal grease thickness≤50um Warmeleitpaste Dicke≤50um λ = 0,61 W/mK					1,63 1,0758		K/W
Coupled thermal resistance inverter diode-transistor Gekoppelte Wärmewiderstand Wechselrichter Diode-Transistor	R_{thJH}		Thermal grease thickness≤50um Warmeleitpaste Dicke≤50um λ = 0,61 W/mK					TBD		K/W

Characteristic values

Description	Symbol	Conditions					Datasheet values			Unit
		T(C°)	Other conditions (Rgon-Rgoff)	VGE(V) VGS(V)	VR(V) VCE(V) VDS(V)	IC(A) IF(A) Id(A)	Min	Typ	Max	
Diode Inverter **Diode Wechselrichter**										
Diode forward voltage Durchlaßspannung	V_F	Tj=25°C Tj=125°C				15		1,69 1,39	2,2	V
Peak reverse recovery current Rückstromspitze	I_{RRM}	Tj=25°C Tj=125°C	Rgon=40Ohm	15	300	15		 27,3		A
Reverse recovery time Sperreverzögerungszeit	t_{rr}	Tj=25°C Tj=125°C	Rgon=40Ohm	15	300	15		 56		ns
Reverse recovered charge Sperrverzögerungsladung	Q_{rr}	Tj=25°C Tj=125°C	Rgon=40Ohm	15	300	15		 0,86		uC
Reverse recovered energy Sperrverzögerungsenergie	Erec	Tj=25°C Tj=125°C	Rgon=40Ohm	15	300	15		 0,127		mWs
Thermal resistance chip to heatsink per chip Wärmewiderstand Chip-Kühlkörper pro Chip	R_{thJH}		Thermal grease thickness≤50um Warmeleitpaste Dicke≤50um λ = 0,61 W/mK					2,43 1,6038		K/W
Coupled thermal resistance inverter transistor-diode Gekoppelte Wärmewiderstand Wechselrichter Transistor-Diode	R_{thJH}		Thermal grease thickness≤50um Warmeleitpaste Dicke≤50um λ = 0,61 W/mK					TBD		K/W
NTC-Thermistor **NTC-Widerstand**										
Rated resistance Nennwiderstand	R_{25}	Tj=25°C	Tol. ±5%				20,9	22	23,1	kOhm
Deviation of R100 Abweichung von R100	$D_{R/R}$	Tc=100°C	R100=1503Ohm					2,9		%/K
Power dissipation given Epcos-Typ Verlustleistung Epcos-Typ angeben	P	Tj=25°C						210		mW
B-value B-Wert	$B_{(25/100)}$	Tj=25°C	Tol. ±3%					3980		K

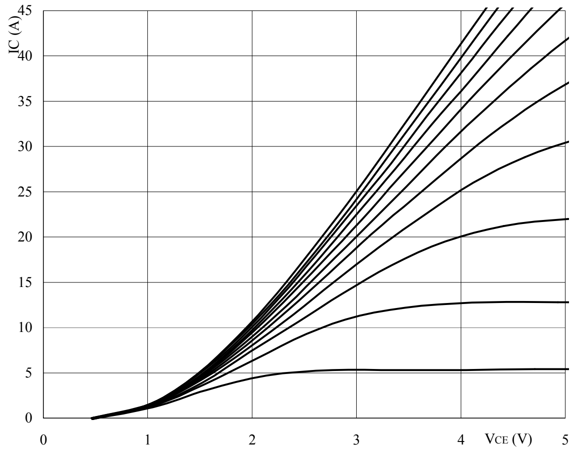
Output inverter

Figure 1. Typical output characteristics
Output inverter IGBT
Ic= f(VCE)



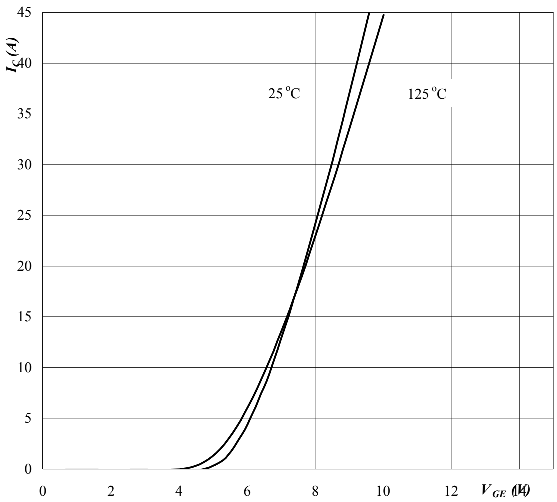
parameter: tp = 250 ms Tj = 25 °C
VGE parameter: from: 6 V to 16 V
in 1 V steps

Figure 2. Typical output characteristics
Output inverter IGBT
Ic= f(VCE)



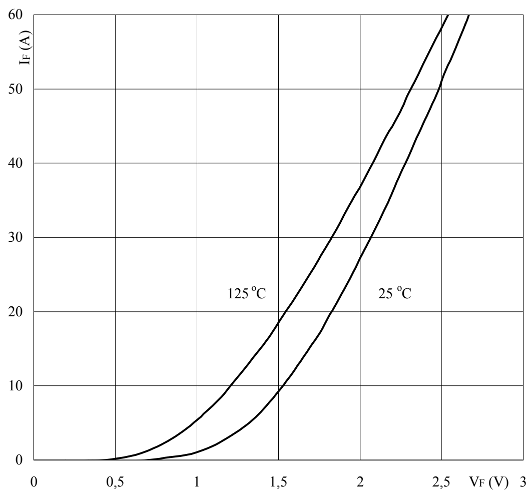
parameter: tp = 250 ms Tj = 125 °C
VGE parameter: from: 6 V to 16 V
in 1 V steps

Figure 3. Typical transfer characteristics
Output inverter IGBT
Ic= f(VGE)



parameter: tp = 250 ms VCE = 17 V

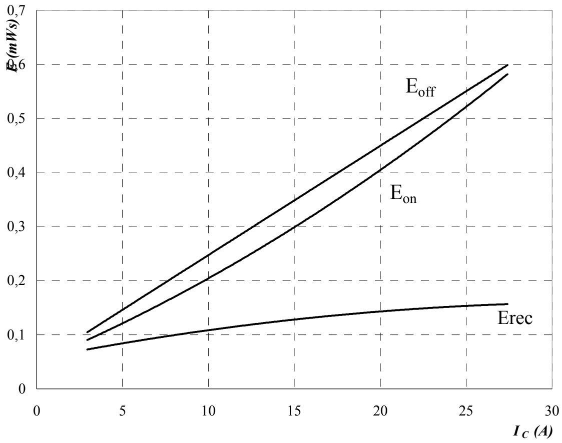
Figure 4. Typical diode forward current as a function of forward voltage
Output inverter FRED IF=f(VF)



parameter: tp = 250 ms

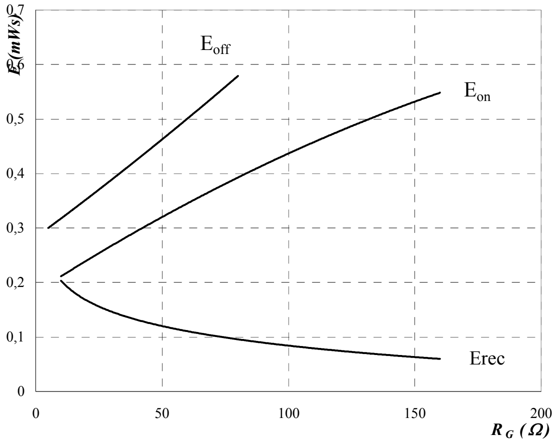
Output inverter

Figure 5. Typical switching energy losses as a function of collector current
Output inverter IGBT
E = f (Ic)



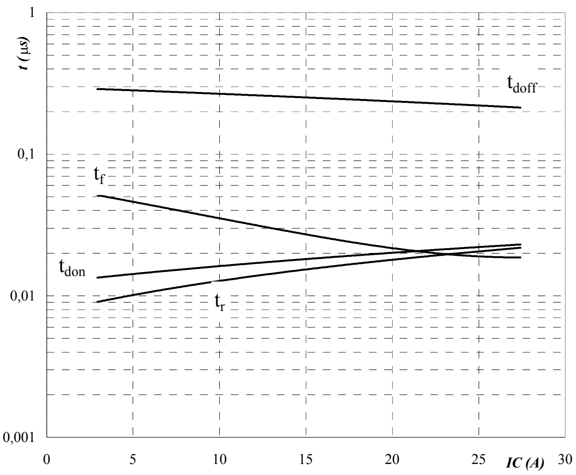
inductive load, Tj = 125 °C
VCE = 300 V
VGE= 15 V
RGon = 2*RGoff = 40 Ohm

Figure 6. Typical switching energy losses as a function of gate resistor
Output inverter IGBT
E = f (RG)



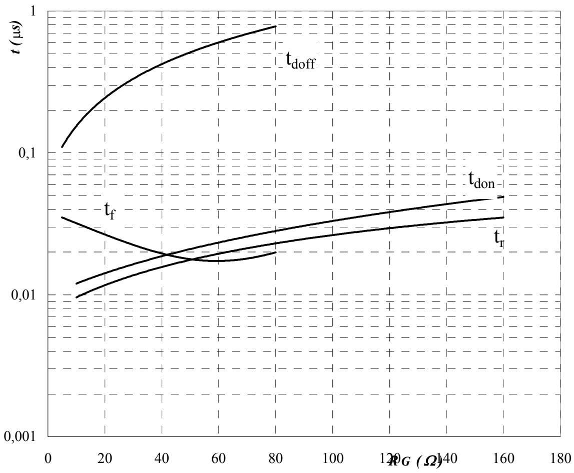
inductive load, Tj = 125 °C
VCE = 300 V
VGE= 15 V
Ic = 15 A

Figure 7. Typical switching times as a function of collector current
Output inverter IGBT
t = f (Ic)



inductive load, Tj = 125 °C
VCE = 300 V
VGE= 15 V
RGon = 2*RGoff = 40 Ohm

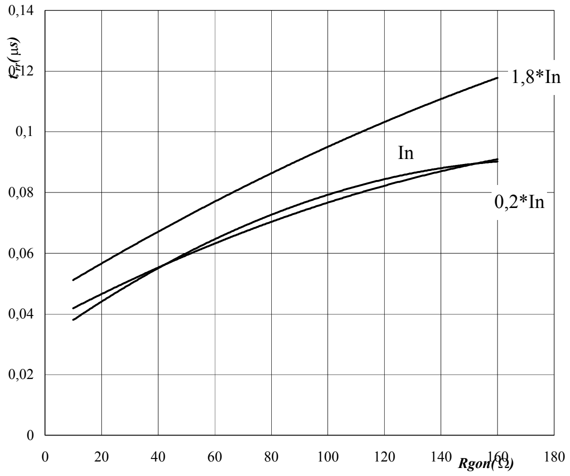
Figure 8. Typical switching times as a function of gate resistor
Output inverter IGBT
t = f (RG)



inductive load, Tj = 125 °C
VCE = 300 V
VGE= 15 V
Ic = 15 A

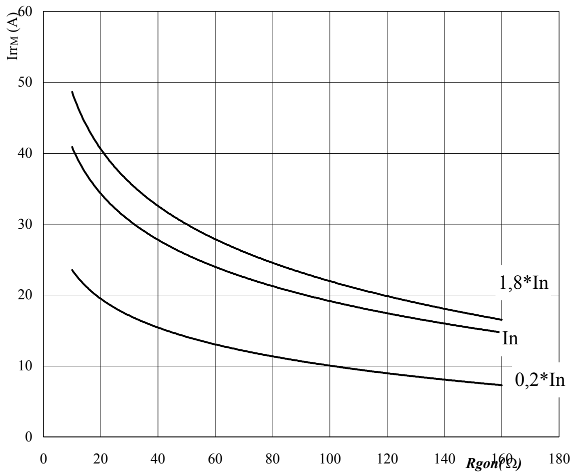
Output inverter

Figure 9. Typical reverse recovery time as a function of gate resistor
Output inverter FRED diode
trr = f (Rgon)



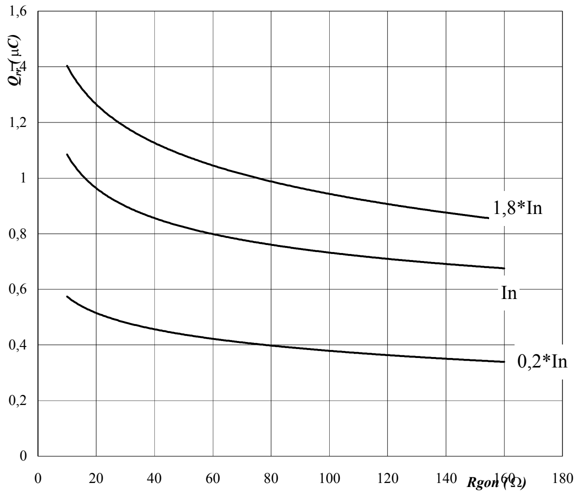
Tj = 125 °C
VR = 300 V
In= 15 A

Figure 10. Typical reverse recovery current as a function of gate resistor
Output inverter FRED diode
IRRM = f (Rgon)



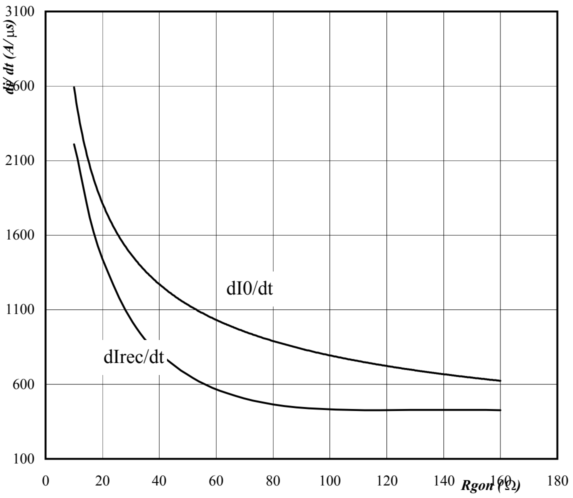
Tj = 125 °C
VR = 300 V
In= 15 A

Figure 11. Typical reverse recovery charge as a function of gate resistor
Output inverter FRED diode
Qrr = f (Rgon)



Tj = 125 °C
VR = 300 V
In= 15 A

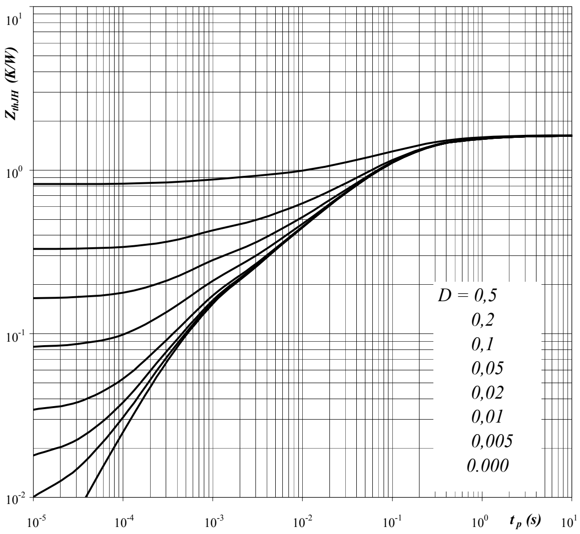
Figure 12. Typical diode peak rate of fall of forward and reverse recovery current as a function of gate resistor
Output inverter FRED diode
di0/dt,dIrec/dt= f (Rgon)



Tj = 125 °C
VR = 300 V
I_F= 15 A

Output inverter

Figure 13. IGBT transient thermal impedance as a function of pulse width
ZthJH = f(tp)

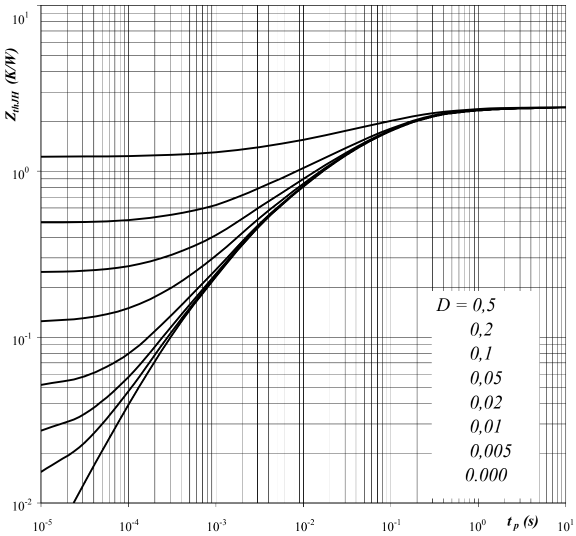


Parameter: D = tp / T RthJH= 1,63 K/W

IGBT thermal model values

R (C/W)	Tau (s)
0,03	4,6E+01
0,14	1,2E+00
0,62	1,6E-01
0,50	4,1E-02

Figure 14. FRED transient thermal impedance as a function of pulse width
ZthJH = f(tp)



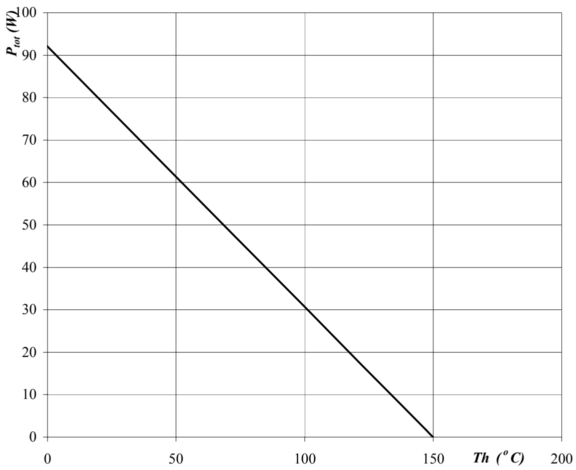
Parameter: D = tp / T RthJH= 2,43 K/W

FRED thermal model values

R (C/W)	Tau (s)
0,03	4,2E+01
0,15	1,8E+00
0,67	2,0E-01
0,73	5,4E-02
0,51	1,1E-02

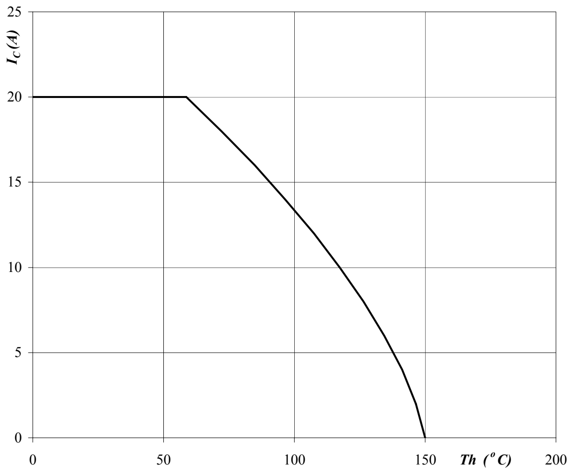
Output inverter

Figure 15. Power dissipation as a function of heatsink temperature
Output inverter IGBT
Ptot = f (Th)



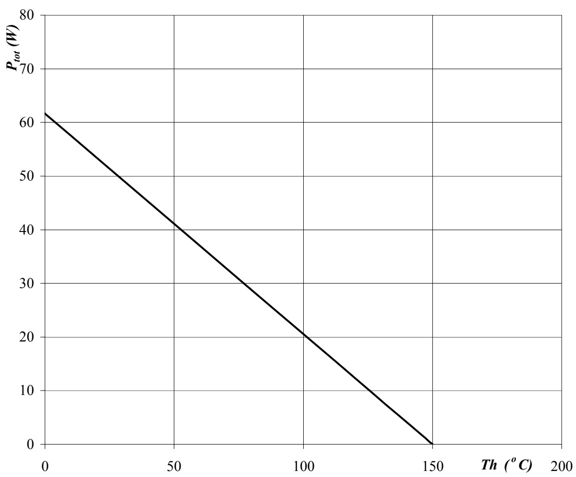
parameter: Tj = 150°C

Figure 16. Collector current as a function of heatsink temperature
Output inverter IGBT
Ic = f (Th)



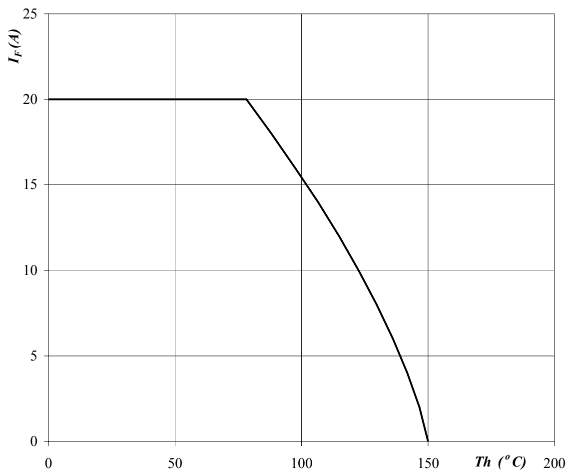
parameter: Tj = 150°C
V_{GE}= 15 V

Figure 17. Power dissipation as a function of heatsink temperature
Output inverter FRED
Ptot = f (Th)



parameter: Tj = 150°C

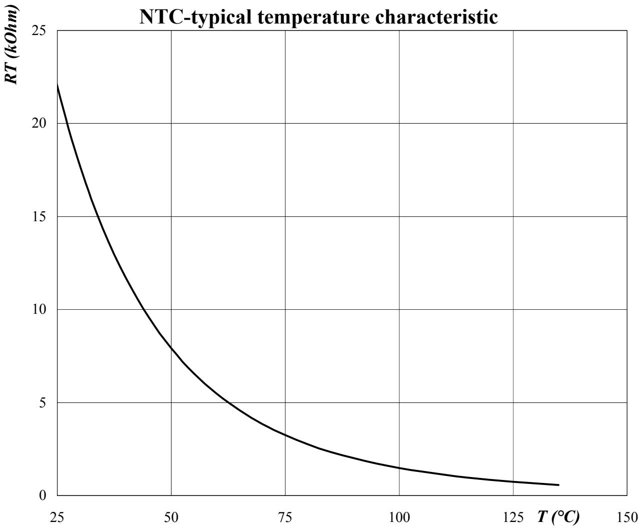
Figure 18. Forward current as a function of heatsink temperature
Output inverter FRED
IF = f (Th)



parameter: Tj = 150°C

Thermistor

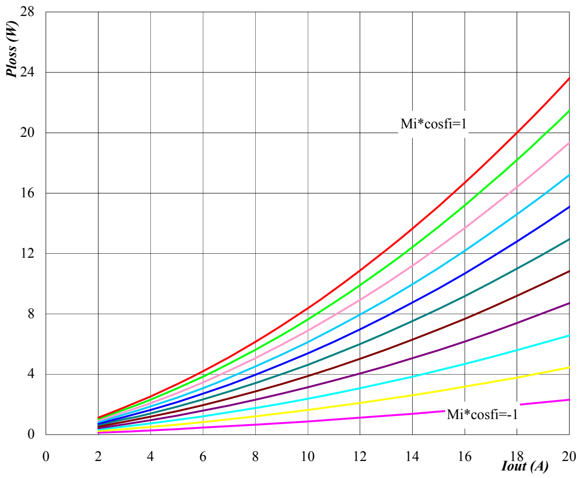
Figure 23. Typical NTC characteristic as a function of temperature
NTC
RT = f (T)



Output inverter application

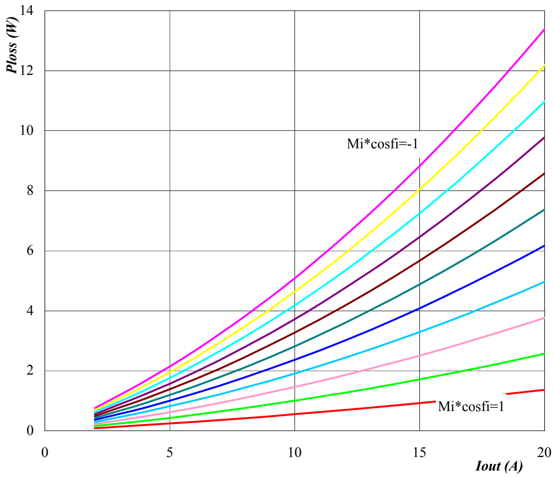
General conditions: 3 phase SPWM, Vgeon= 15 V Vgeoff=0V Rgon= 40 ohms Rgoff= 20 ohms

Figure 1. Typical avarage static loss as a function of output current
IGBT Ploss=f(Iout)



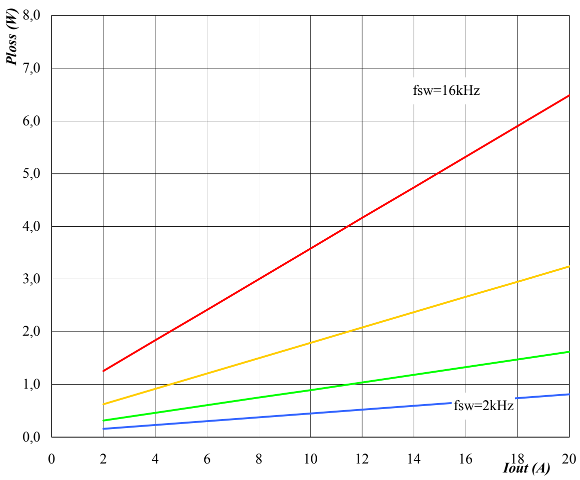
Conditions: Tj=125°C
Modulation index * cosfi
parameter Mi*cosfi from -1,00 to 1,00
in 0,20 steps

Figure 2. Typical avarage static loss as a function of output current
FRED Ploss=f(Iout)



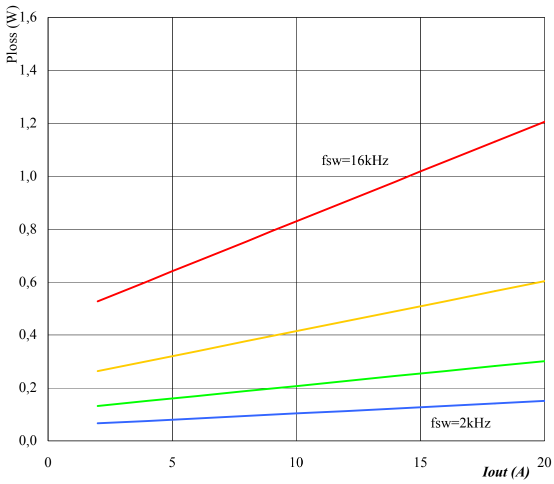
Conditions: Tj=125°C
Modulation index * cosfi
parameter Mi*cosfi from -1,00 to 1,00
in 0,20 steps

Figure 3. Typical avarage switching loss as a function of output current
IGBT Ploss=f(Iout)



Conditions: Tj=125C
DC link= 320 V
Switching freq. fsw from 2 kHz to 16 kHz
parameter in * 2 steps

Figure 4. Typical avarage switching loss as a function of output current
FRED Ploss=f(Iout)



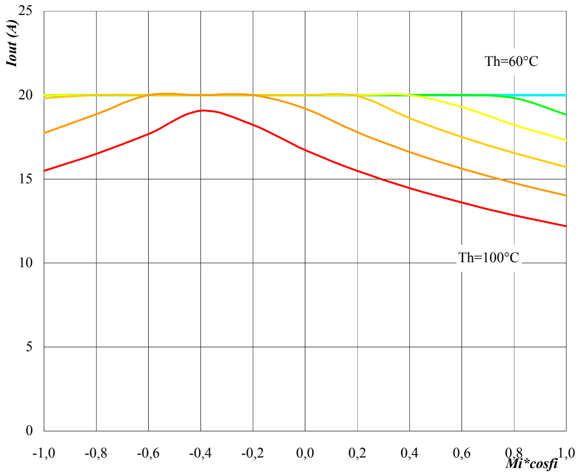
Conditions: Tj=125C
DC link= 320 V
Switching freq. fsw from 2 kHz to 16 kHz
parameter in * 2 steps

Output inverter application

General conditions: 3 phase SPWM, Vgeon= 15 V Vgeoff=0V Rgon= 40 ohms Rgoff= 20 ohms

Figure 5. Typical available 50Hz output current as a function of Mi*cosfi

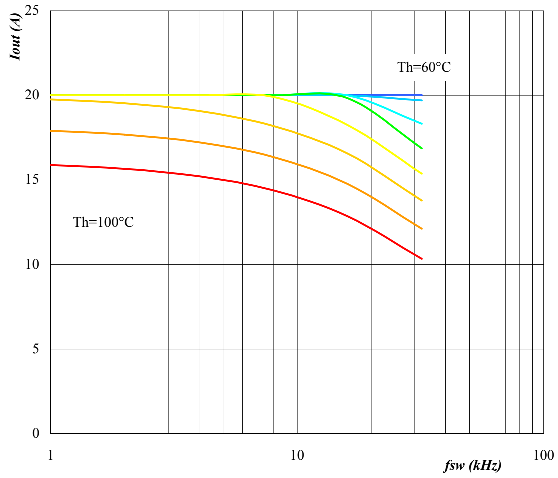
Phase Iout=f(Mi*cosfi)



Conditions:	Tj=125C			
	DC link=	320 V		
	fsw=	16 kHz		
Heatsink temp.	Th from	60 °C to	100 °C	
parameter	in	5 °C	steps	

Figure 6. Typical available 50Hz output current as a function of switching frequency

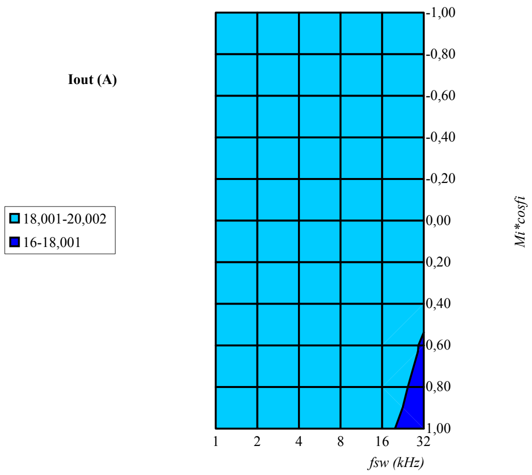
Phase Iout=f(fsw)



Conditions:	Tj=125C			
	DC link=	320 V		
	Mi*cosfi=	0,8		
Heatsink temp.	Th from	60 °C to	100 °C	
parameter	in	5 °C	steps	

Figure 7. Typical available 50Hz output current as a function of Mi*cosfi and fsw

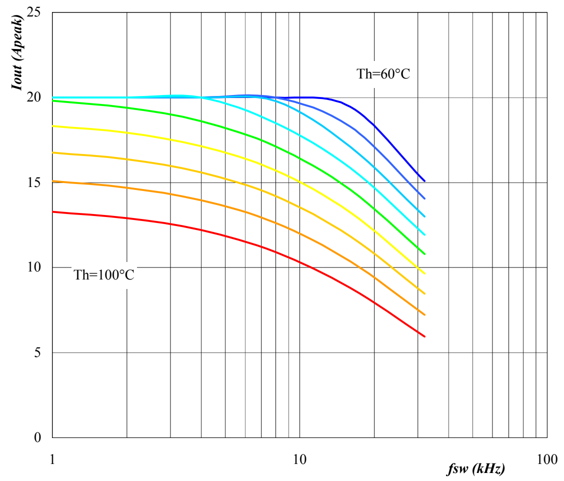
Phase Iout=f(fsw,Mi*cosfi)



Conditions:	Tj=125C	
	DC link=	320 V
	Th=	80 °C

Figure 8. Typical available 0Hz output current as a function of switching frequency

Phase Ioutpeak=f(fsw)



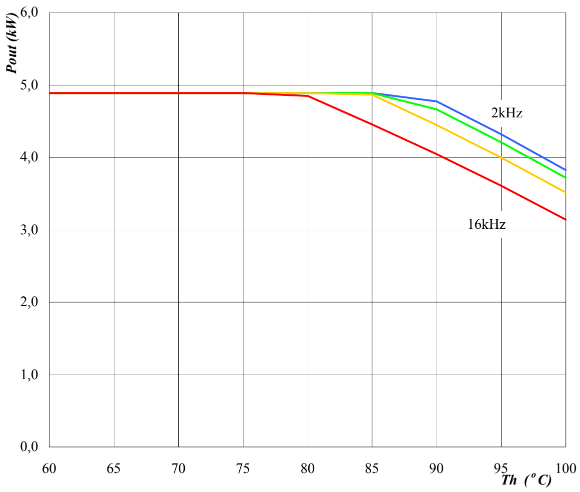
Conditions:	Tj=125C			
	DC link=	320 V		
Heatsink temp.	Th from	60 °C to	100 °C	
parameter	in	5 °C	steps	

Output inverter application

General conditions: 3 phase SPWM, Vgeon= 15 V Vgeoff=0V Rgon= 40 ohms Rgoff= 20 ohms

Figure 9. Typical available electric peak output power as a function of heatsink temperature

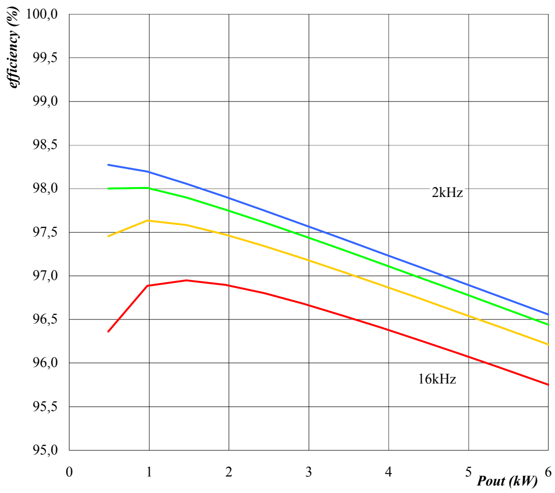
Inverter Pout=f(Th)



Conditions: Tj=125C
DC link= 320 V
Modulation index Mi= 1
cosfi= 0,80
Switching freq. parameter fsw from 2 kHz to 16 kHz in * 2 steps

Figure 10. Typical efficiency as a function of output power

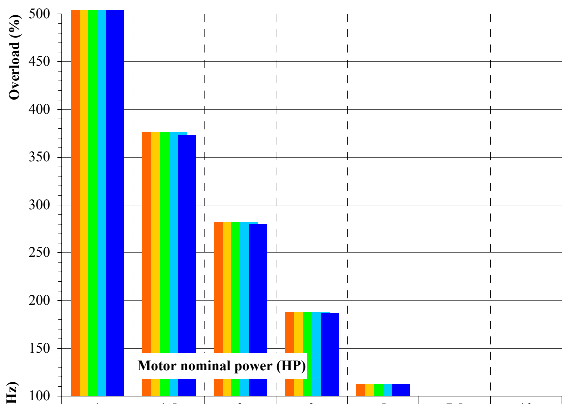
Inverter efficiency=f(Pout)



Conditions: Tj=125C
DC link= 320 V
Modulation index Mi= 1
cosfi= 0,80
Switching freq. parameter fsw from 2 kHz to 16 kHz in * 2 steps

Figure 11. Typical available overload factor as a function of motor power and switching frequency

Inverter Ppeak/Pnom=f(Pnom,fsw)



Switching frequency (kHz)	1	1,5	2	3	5	7,5	10
1	565	377	282	188	113	0	0
2	565	377	282	188	113	0	0
4	565	377	282	188	113	0	0
8	565	377	282	188	113	0	0
16	560	373	280	187	112	0	0

Conditions: Tj=125C
DC link= 320 V
Modulation index Mi= 1
cosfi= 0,8
Switching freq. parameter fsw from 1 kHz to 16 kHz in * 2 steps
Heatsink temperature= 80 °C
Motor efficiency= 0,85